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NP110N04PUK

R07DS0570EJ0200

Rev.2.00

May 24, 2018

MOS FIELD EFFECT TRANSISTOR

Description

The NP110N04PUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance
 $R_{DS(on)} = 1.4 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 55 \text{ A)}$
- Low C_{iss} : $C_{iss} = 10500 \text{ pF TYP. (} V_{DS} = 25 \text{ V)}$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing		Package
NP110N04PUK-E1-AY *1	Pure Sn (Tin)	Tape 800 p/reel	Taping (E1 type)	TO-263 (MP-25ZP)
NP110N04PUK-E2-AY *1			Taping (E2 type)	

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 110	A
Drain Current (pulse) *1, 3	$I_{D(pulse)}$	± 440	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	348	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.8	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 175	$^\circ\text{C}$
Repetitive Avalanche Current *2, 3	I_{AR}	72	A
Repetitive Avalanche Energy *2, 3	E_{AR}	518	mJ

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-C)} *3$	0.43	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)} *3$	83.3	$^\circ\text{C/W}$

Notes: *1 $T_C = 25^\circ\text{C}$, $P_w \leq 10 \text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

*2 $R_G = 25 \text{ }\Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

*3 Not subject of production test. Verified by design/characterization.

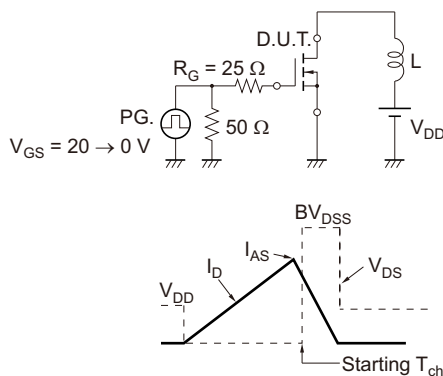
Electrical Characteristics ($T_A = 25^\circ\text{C}$)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$
Gate Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
Forward Transfer Admittance *1	$ y_{fs} $	60	120	—	S	$V_{DS} = 5\text{ V}$, $I_D = 55\text{ A}$
Drain to Source On-state Resistance *1	$R_{DS(on)}$	—	1.15	1.40	m Ω	$V_{GS} = 10\text{ V}$, $I_D = 55\text{ A}$
Input Capacitance *2	C_{iss}	—	10500	15750	pF	$V_{DS} = 25\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$
Output Capacitance *2	C_{oss}	—	1600	2400	pF	
Reverse Transfer Capacitance *2	C_{rss}	—	540	980	pF	
Turn-on Delay Time *2	$t_{d(on)}$	—	38	90	ns	$V_{DD} = 20\text{ V}$, $I_D = 55\text{ A}$ $V_{GS} = 10\text{ V}$ $R_G = 0\text{ }\Omega$
Rise Time *2	t_r	—	21	60	ns	
Turn-off Delay Time *2	$t_{d(off)}$	—	140	280	ns	
Fall Time *2	t_f	—	20	50	ns	
Total Gate Charge *2	Q_G	—	198	297	nC	$V_{DD} = 32\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 110\text{ A}$
Gate to Source Charge	Q_{GS}	—	50	—	nC	
Gate to Drain Charge	Q_{GD}	—	48	—	nC	
Body Diode Forward Voltage *1	$V_{F(S-D)}$	—	0.9	1.5	V	$I_F = 110\text{ A}$, $V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}	—	83	—	ns	$I_F = 110\text{ A}$, $V_{GS} = 0\text{ V}$
Reverse Recovery Charge	Q_{rr}	—	130	—	nC	$di/dt = 100\text{ A}/\mu\text{s}$

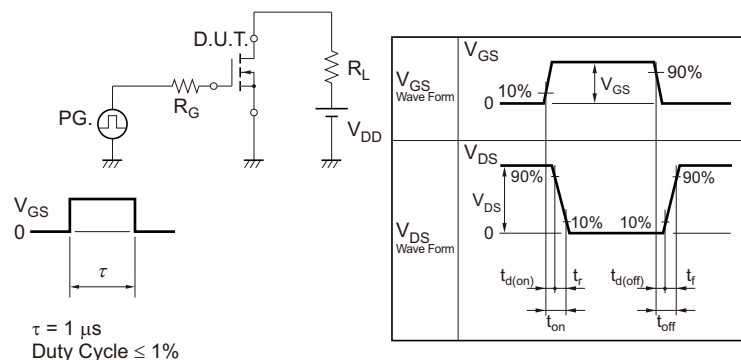
Note: *1 Pulsed test

Note: *2 Not subject of production test. Verified by design/characterization.

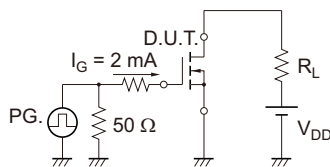
TEST CIRCUIT 1 AVALANCHE CAPABILITY



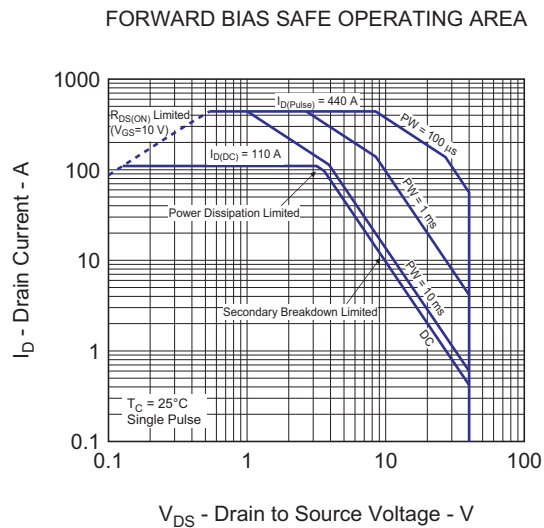
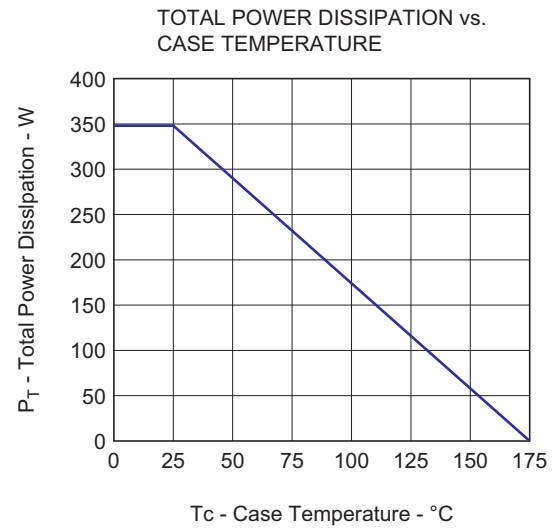
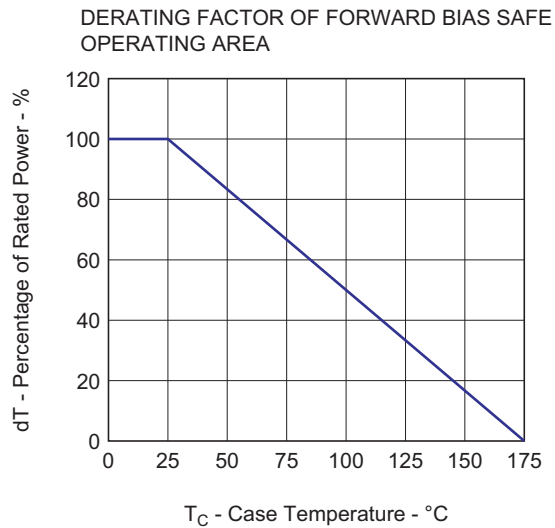
TEST CIRCUIT 2 SWITCHING TIME



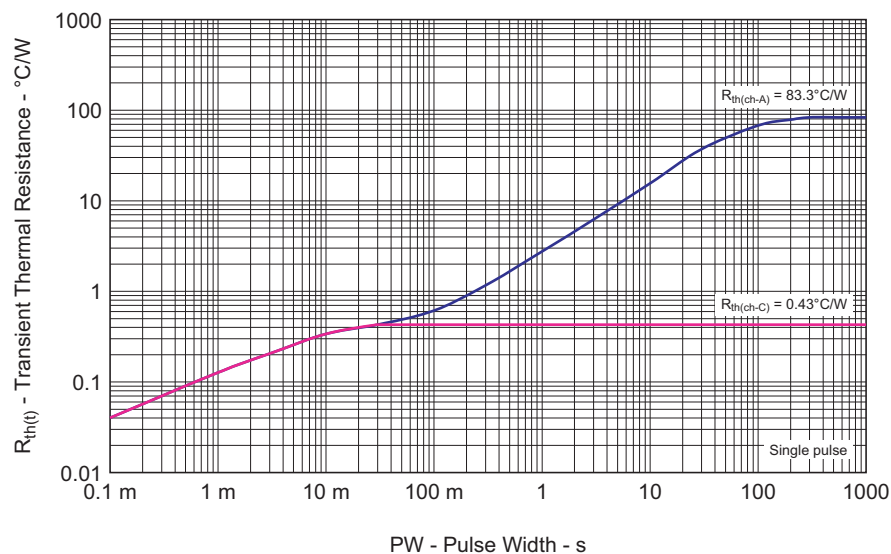
TEST CIRCUIT 3 GATE CHARGE

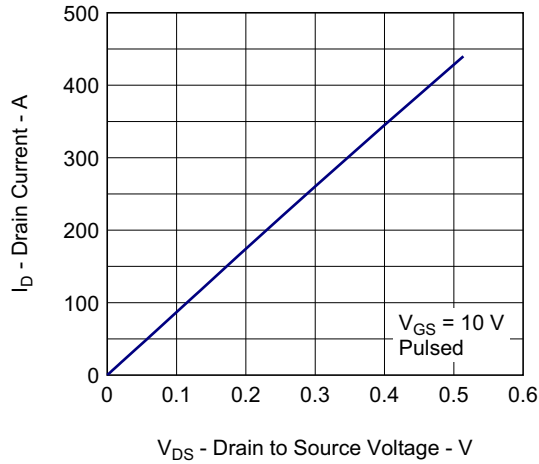


Typical Characteristics ($T_A = 25^\circ\text{C}$)

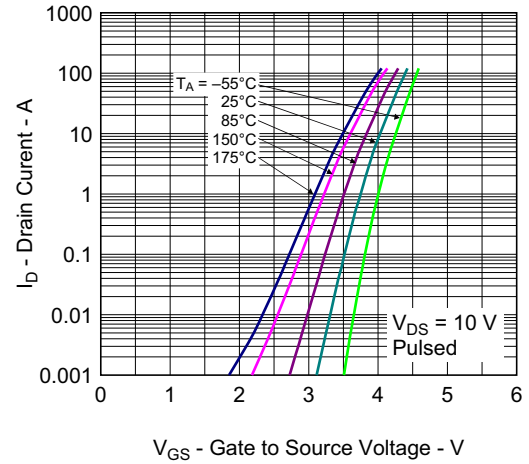
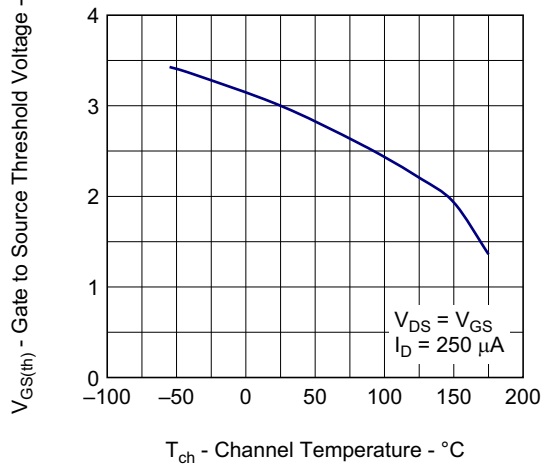
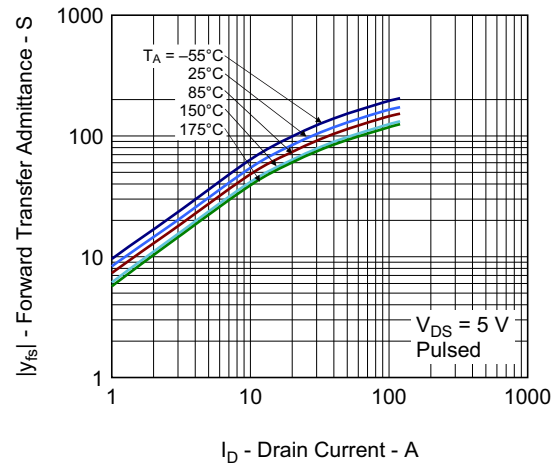
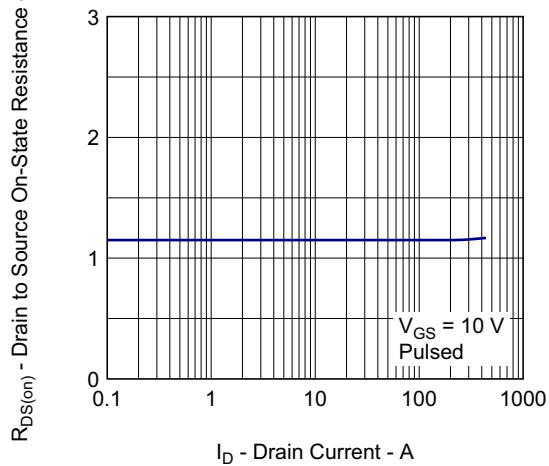
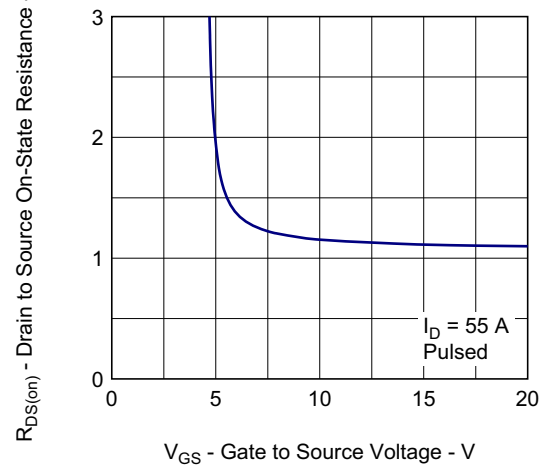


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

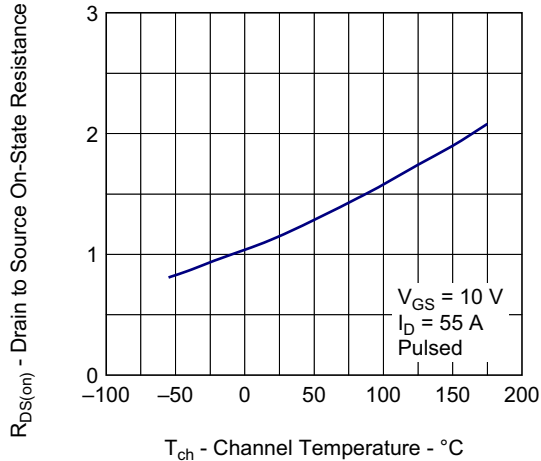


DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

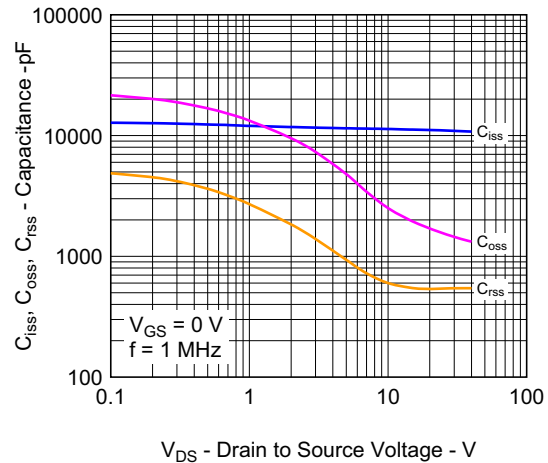
FORWARD TRANSFER CHARACTERISTICS

GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

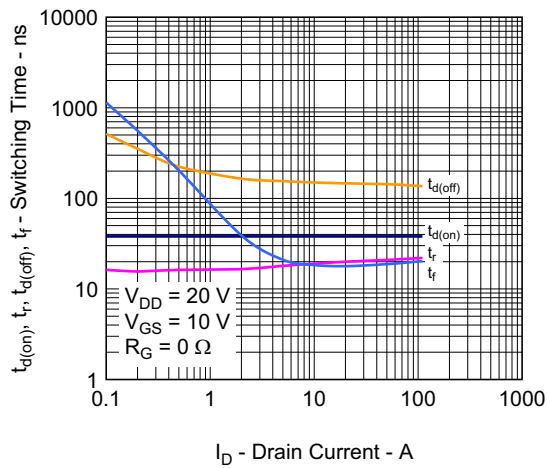
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



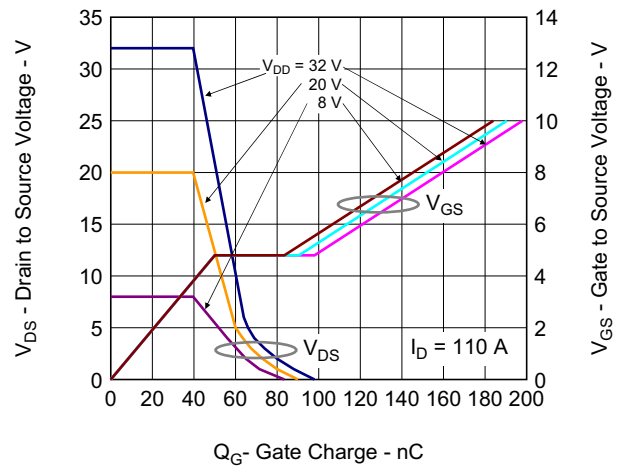
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



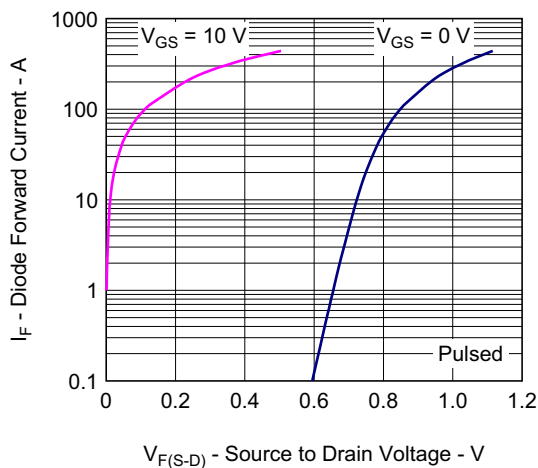
SWITCHING CHARACTERISTICS



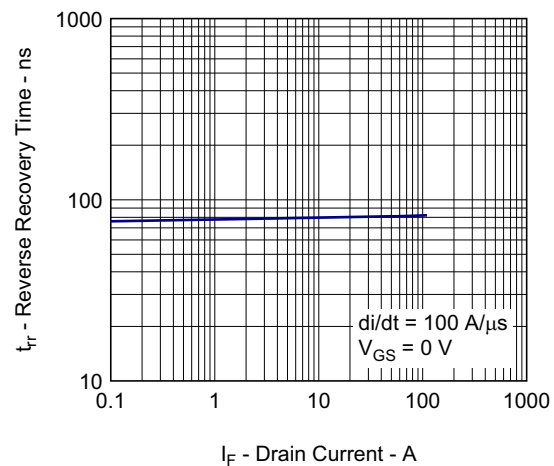
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

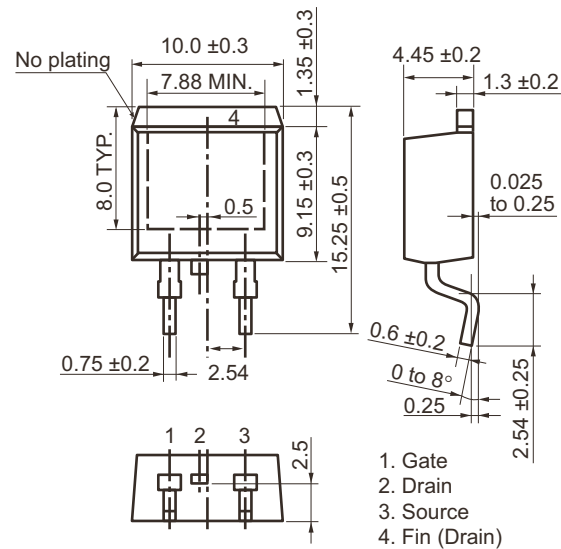


REVERSE RECOVERY TIME vs. DRAIN CURRENT

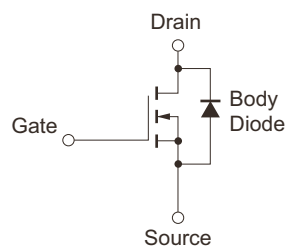


Package Drawing (Unit: mm)

TO-263 (MP-25ZP) (Mass: 1.5 g TYP.)



Equivalent Circuit



Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History	NP110N04PUK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Nov 17, 2011	—	First Edition Issued
2.00	May 24 ,2018	1	Note 3 was added
		2	Note 2 was added

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